

<p><b>U.S. Department of Commerce, Patent and Trademark Office</b></p> <p>INFORMATION DISCLOSURE STATEMENT BY APPLICANT            (Use several sheets if necessary)</p>	<b>Application No.:</b>	Unknown
	<b>Filing Date:</b>	Unknown
	<b>First Named Inventor:</b>	Hamza Yilmaz
	<b>Group Art Unit:</b>	Unknown
	<b>Examiner Name:</b>	Unknown
	<b>Confirmation No.:</b>	Unknown
	<b>Attorney Docket No.:</b>	YMZ004 US

## **U.S. Patent Documents**

## Foreign Patent Documents

**Other Art (Including Author, Title, Date, Pertinent Pages, Etc.)**

	<p>3. Jongdae Kim et al., "High-Density Trench DMOSFETs Employing Two Step Trench Technique and Trench Contact Structure", ISPSD-2003 Proceedings, pp. 1-4</p> <p>4. Il-Yong Park et al., "Novel Process Techniques for Fabricating High Density Trench MOSFETs with Self-Aligned N<sup>+</sup>/P<sup>+</sup> Source Formed on the Trench Side Wall", ISPSD-2003 Proceedings, pp. 1-4.</p> <p>5. M.A.A. In 'tZandt, et al., "Record-low 4mΩ mm<sup>2</sup> specific on-resistance for 20V Trench MOSFETs", ISPSD-2003 Proceedings, pp. 1-4.</p> <p>6. Mohamed Darwish et al., "A New Power W-Gated Trench MOSFET (WMOSFET) with High Switching Performance", ISPSD-2003 Proceedings, pp 1-4.</p> <p>7. Syotaro Ono et al., "30V New Fine Trench MOSFET with Ultra Low On-Resistance", ISPSD-2003 Proceedings, pp. 1-4.</p>
	
	

Examiner: <i>John Bal</i>	Date Considered: <i>1/13/05</i>
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\* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.